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## Figure Captions

### Chapter 2

Fig. 2-1. The layer structure and the growth conditions for the Ge film grown on the Si substrate with  $\text{Ge}_x\text{Si}_{1-x}$  metamorphic buffer layers. Note that  $\text{Ge}_x\text{Si}_{1-x}$  was grown at two growth rates, the Ge composition set at 80% and 90%, and the Si substrate implanted with high dose  $\text{Si}^+$  ions.

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